

Title (en)

Method and structure for providing improved insulation in VLSI and ULSI circuits.

Title (de)

Verfahren und Struktur zur Herstellung einer Isolierung aus VLSI- und ULSI-Schaltungen.

Title (fr)

Procédé et structure pour modifier l'isolation dans les circuits VLSI et ULSI.

Publication

EP 0373360 A2 19900620 (EN)

Application

EP 89120666 A 19891108

Priority

US 28644388 A 19881216

Abstract (en)

An improved VLSI or ULSI structure and a method of forming the same are provided. The structure starts with a base member having a plurality of supports formed thereon and extending upwardly therefrom. A selectively removable material is deposited on the base member and around the supports. An insulating cap is formed over the supports and the removable material. Access openings are provided through the cover (or base) and the removable material is removed through the access openings. Thereafter a partial vacuum is formed in the space evacuated by the removable material, and the access openings sealed to provide a dielectric medium around the supports and between the base and cap member having a dielectric constant of less than 2.0.

IPC 1-7

H01L 21/90; **H01L 23/522**

IPC 8 full level

H01L 21/768 (2006.01); **H01L 23/522** (2006.01)

CPC (source: EP US)

H01L 21/7682 (2013.01 - EP US); **H01L 21/76885** (2013.01 - EP); **H01L 21/76897** (2013.01 - EP US); **H01L 23/5222** (2013.01 - EP US); **H01L 2924/0002** (2013.01 - EP US)

Cited by

EP2107603A1; US6307265B1; US6064118A; EP0714129A3; US5843836A; DE10200869A1; EP0475646A3; EP1022777A1; EP2107605A1; EP0476625A3; DE10316776A1; DE10316776B4; DE10144847A1; US6368939B1; EP0872887A3; DE10316777A1; DE10316777B4; GB2248072A; GB2248072B; EP0783178A3; US6955950B2; WO9626541A1; US7234237B2; US6306753B1; US7728389B2; US7977166B2; KR100279790B1; US6939734B2; EP2826856A1

Designated contracting state (EPC)

DE FR GB

DOCDB simple family (publication)

EP 0373360 A2 19900620; **EP 0373360 A3 19910227**; **EP 0373360 B1 19951004**; DE 68924468 D1 19951109; DE 68924468 T2 19960530; JP H02218150 A 19900830; JP H0685415 B2 19941026; US 4987101 A 19910122; US 5144411 A 19920901

DOCDB simple family (application)

EP 89120666 A 19891108; DE 68924468 T 19891108; JP 32416689 A 19891215; US 28644388 A 19881216; US 59029090 A 19900928